

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC4880

DESCRIPTION

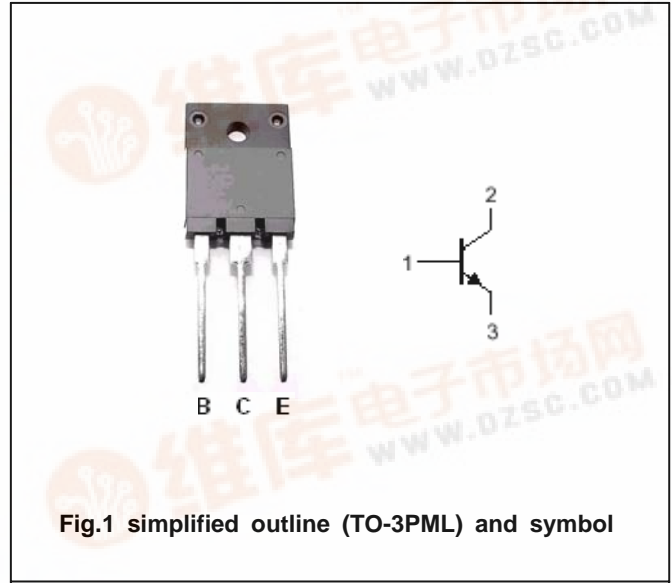
- With TO-3PML package
- High breakdown voltage
- High speed switching

APPLICATIONS

- For color TV display horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(T_a=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1700	V
V _{CEO}	Collector-emitter voltage	Open base	900	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		12	A
P _C	Collector power dissipation	T _C =25°C	100	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon NPN Power Transistors

2SC4880

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA; R _{BE} =∞	900			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10A; I _B =2.5 A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10A; I _B =2.5 A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =1700V; R _{BE} =0			500	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μ A
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	8		40	

Silicon NPN Power Transistors

2SC4880

PACKAGE OUTLINE

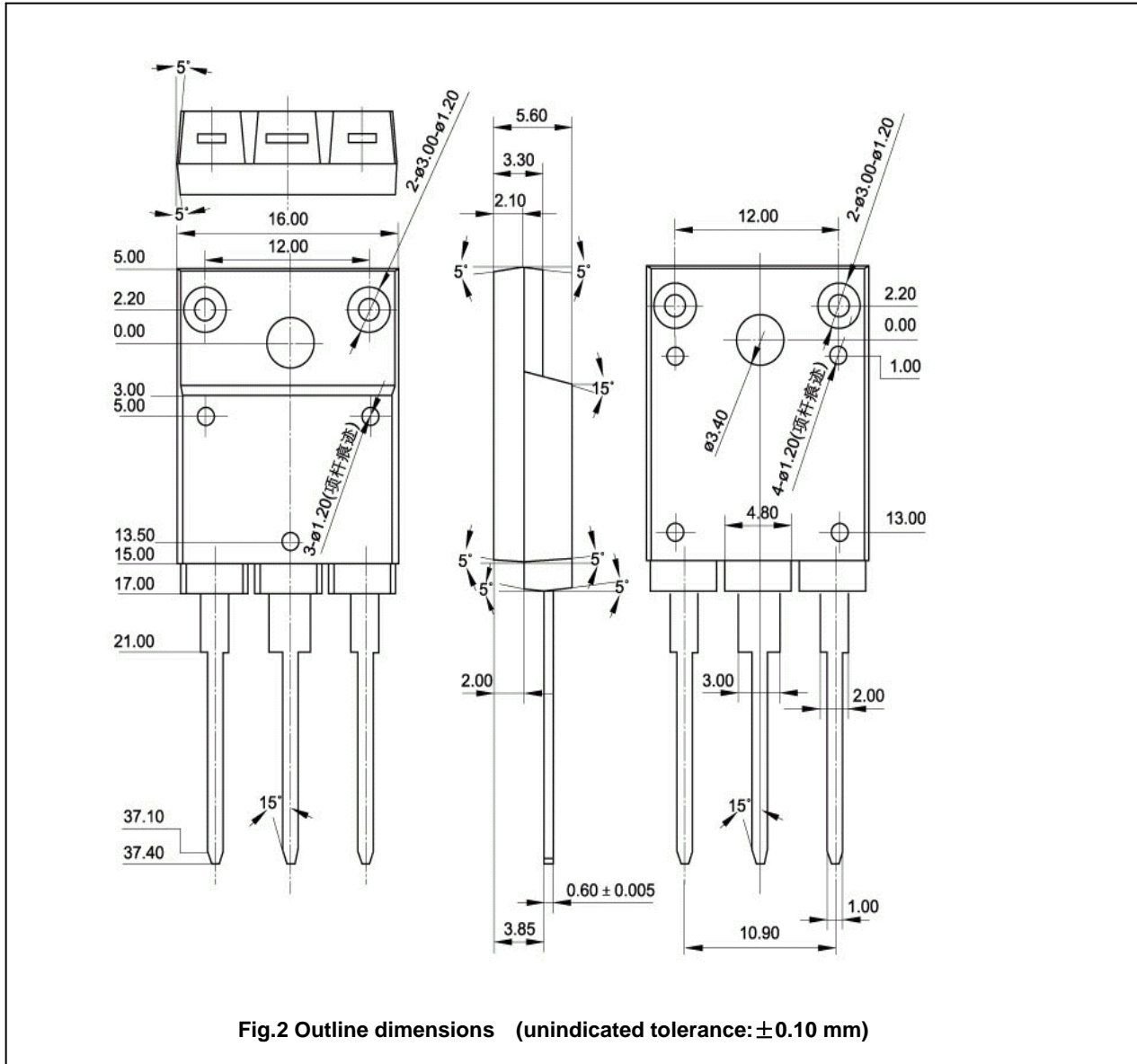


Fig.2 Outline dimensions (unindicated tolerance: ±0.10 mm)